

first nozzle (38; 152) onto the surface of the substrate (2) to be treated.

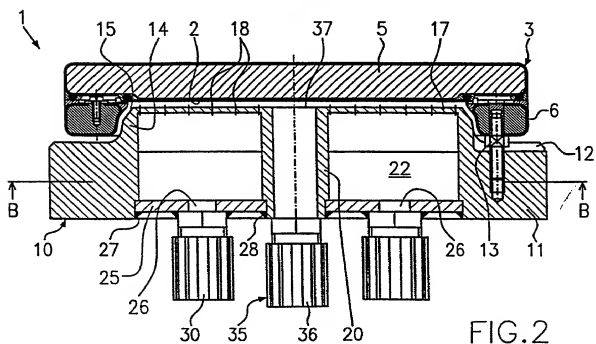
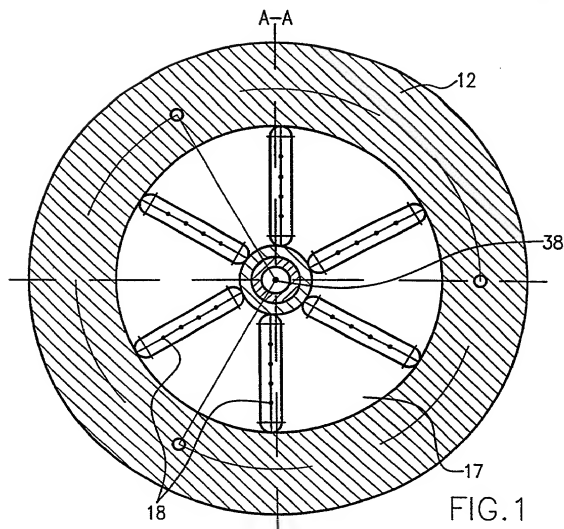
30. Method according to any one of claims 24 through 29, characterized in that a vacuum is applied to the first nozzle (38; 152).

31. Method according to any one of claims 24 through 30, characterized in that a gas is conducted via the second nozzles (18; 142; 144) onto the surface of the substrate (2) to be treated.

32. Method according to any one of claims 24 through 31, characterized by conducting a fluid onto an outer surface of a substrate carrier (3) holding a substrate (2) via at least one nozzle (55) arranged in an overflow collar (50) of the device.

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f Portierung = 10



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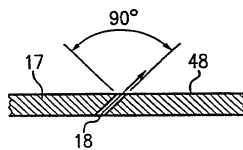
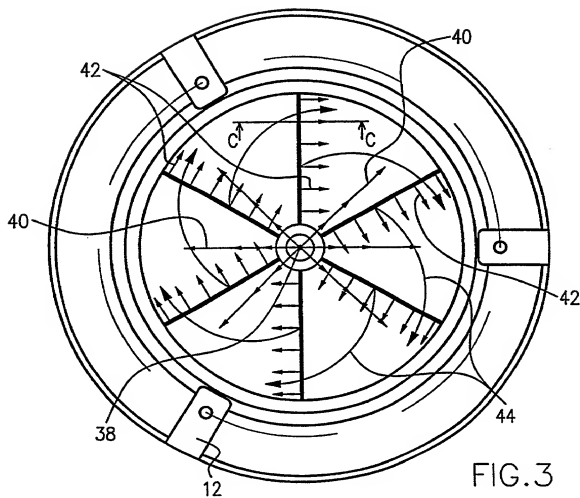


FIG. 4